

# FDMC8878

## N-Channel POWERTRENCH<sup>®</sup> MOSFET 30 V, 16.5 A, 14 mΩ

This N-Channel MOSFET is a rugged gate version of ON Semiconductor's advanced PowerTrench process. It has been optimized for power management applications.

### Features

- $R_{DS(on)} = 14 \text{ m}\Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 9.6 \text{ A}$
- $R_{DS(on)} = 17 \text{ m}\Omega$  (Max.) @  $V_{GS} = 4.5 \text{ V}$ ,  $I_D = 8.7 \text{ A}$
- Low Profile – 0.8 mm Max in MLP 3.3 x 3.3
- These Devices are Pb-Free and are RoHS Compliant

### Application

- DC – DC Conversion

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DS}$	30	V
Gate-to-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$T_C = 25^{\circ}\text{C}$ (Package limited)	$I_D$	16.5	A
	$T_C = 25^{\circ}\text{C}$ (Silicon limited)		38	
	$T_A = 25^{\circ}\text{C}$ (Figure 1)		9.6	
Drain Current	Pulsed	$I_D$	60	A
Power Dissipation	$T_C = 25^{\circ}\text{C}$	$P_D$	31	W
	$T_A = 25^{\circ}\text{C}$ (Figure 1)		2.1	
Operating and Storage Junction Temperature Range		$T_J, T_{STG}$	-55 to +150	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Figure 1)	$R_{\theta JA}$	60	

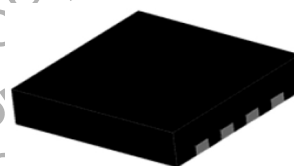
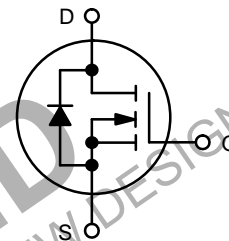
### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Reel Size	Tape Width	Quantity
FDMC8878	FDMC8878	MLP 3.3 x 3.3	13"	12 mm	3000 units

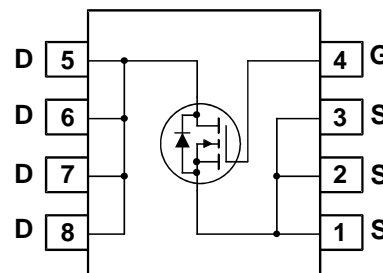


ON Semiconductor<sup>®</sup>

[www.onsemi.com](http://www.onsemi.com)



WDFN8  
CASE 511DH



### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 1 of this data sheet.

**ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
$BV_{DSS}$	Drain-to-Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$	30	–	–	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	–	20	–	mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\ \text{V}$ , $V_{GS} = 0\ \text{V}$	–	–	1	$\mu\text{A}$
		$V_{DS} = 24\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $T_J = 125^\circ\text{C}$	–	–	100	
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$	–	–	$\pm 100$	nA

**ON CHARACTERISTICS**

$V_{GS(th)}$	Gate-to-Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = V_{DS}$	1	1.7	3	V
$\Delta BV_{DSS}/\Delta T_J$	Gate-to-Source Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	–	–5.7	–	mV/ $^\circ\text{C}$
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 9.6\ \text{A}$	–	9.6	14.0	m $\Omega$
		$V_{GS} = 4.5\ \text{V}$ , $I_D = 8.7\ \text{A}$	–	12.1	17.0	
		$V_{GS} = 10\ \text{V}$ , $I_D = 9.6\ \text{A}$ , $T_J = 125^\circ\text{C}$	–	13.5	20.0	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\ \text{V}$ , $I_D = 9.6\ \text{A}$	–	35	–	S

**DYNAMIC CHARACTERISTICS**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$	–	1000	1230	pF
$C_{oss}$	Output Capacitance		–	183	255	pF
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\ \text{MHz}$	–	118	180	pF
$R_g$	Reverse Transfer Capacitance		–	1.1	–	$\Omega$

**SWITCHING CHARACTERISTICS**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\ \text{V}$ , $I_D = 9.6\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$	–	8	16	ns
$t_r$	Rise Time		–	4	10	
$t_{d(off)}$	Turn-Off Delay Time		–	20	36	
$t_f$	Fall Time		–	3	10	
$Q_{g(tot)}$	Total Gate Charge	$V_{GS} = 10\ \text{V}$ , $V_{DD} = 15\ \text{V}$ , $I_D = 9.6\ \text{A}$	–	18	26	nC
$Q_{gs}$	Gate-to-Source Gate Charge		–	2.8	–	
$Q_{gd}$	Gate-to-Drain "Miller" Charge		–	3.9	–	

**DRAIN-SOURCE DIODE CHARACTERISTICS**

$V_{SD}$	Source-to-Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$ , $I_S = 9.6\ \text{A}$ (Note 2)	–	0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 9.6\ \text{A}$ , $di/dt = 100\ \text{A}/\mu\text{s}$	–	23	35	ns
$Q_{rr}$	Reverse Recovery Charge		–	14	21	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

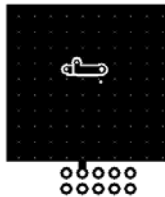


Figure 1.

a.  $60^\circ\text{C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper

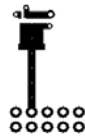


Figure 2.

b.  $135^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

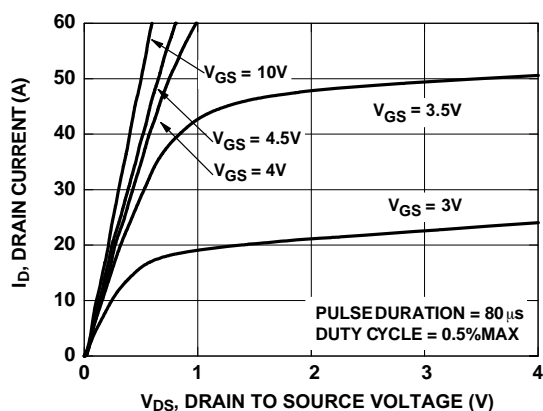
TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Figure 3. Gate Charge Characteristics

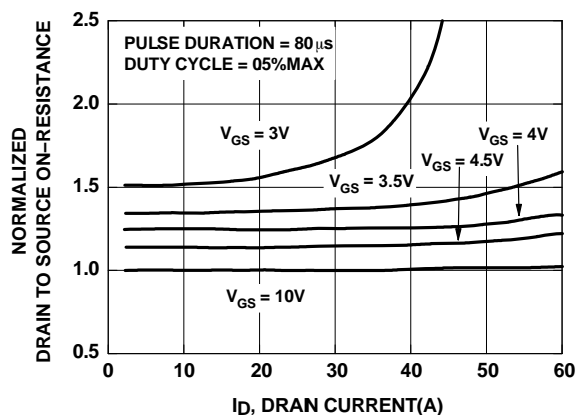


Figure 4. Capacitance vs. Drain to Source Voltage

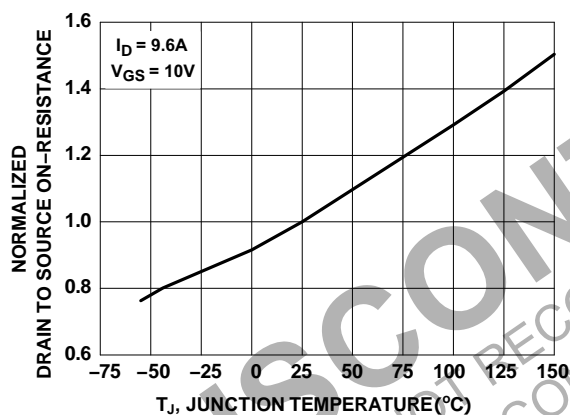


Figure 5. Unclamped Inductive Switching Capability

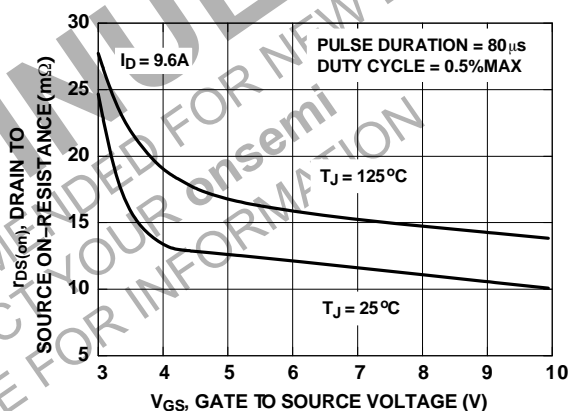


Figure 6. Maximum Continuous Drain Current vs. Ambient Temperature

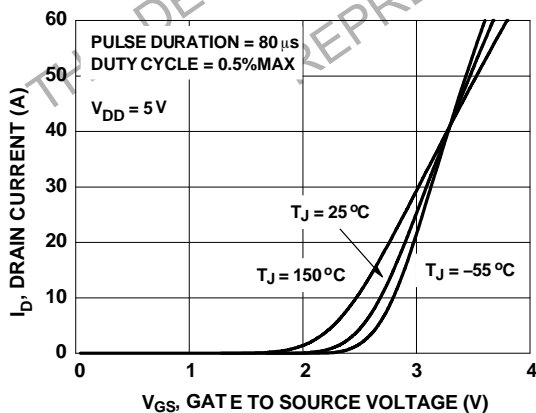


Figure 7. Forward Bias Safe Operating Area

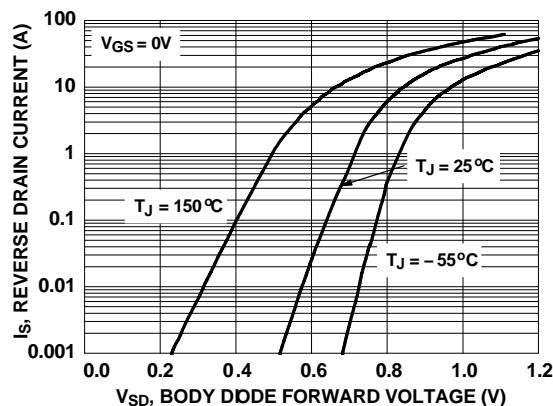


Figure 8. Single Pulse Maximum Power Dissipation

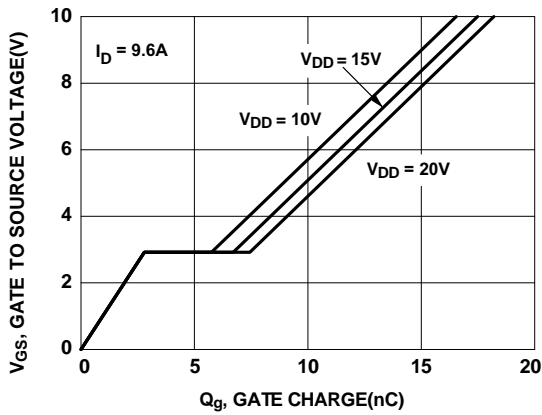
TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Figure 9. On-Region Characteristics

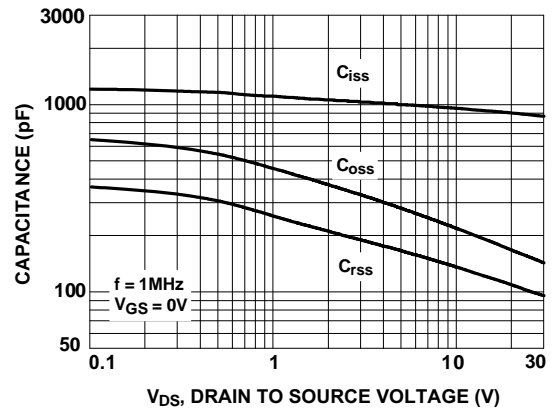


Figure 10. Transfer Characteristics

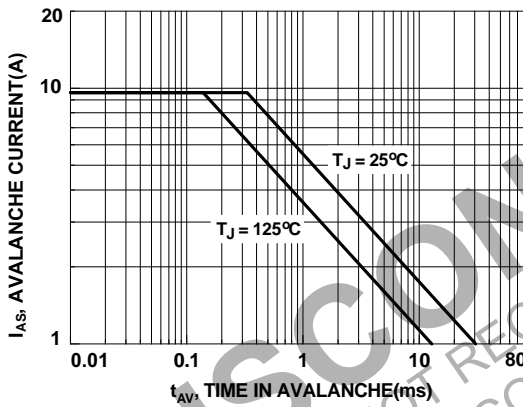


Figure 11. On-Resistance Variation vs. Drain Current and Gate Voltage

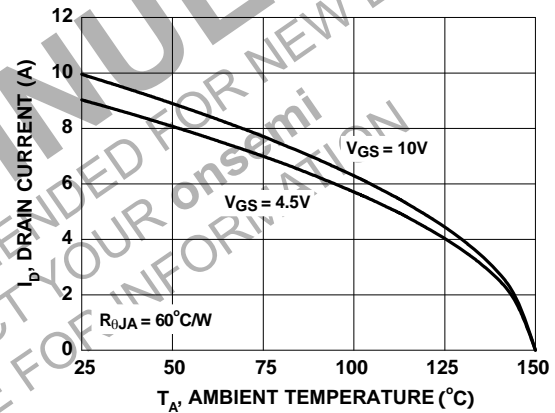


Figure 12. Body Diode Forward Voltage Variation vs. Source Current and Temperature

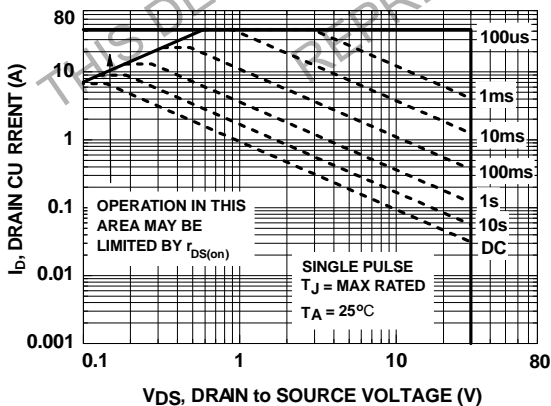


Figure 13. Capacitance Characteristics

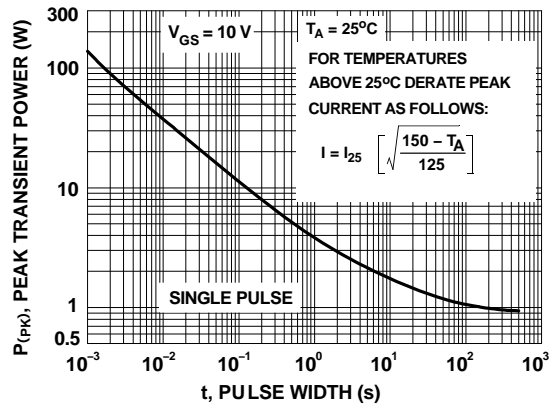
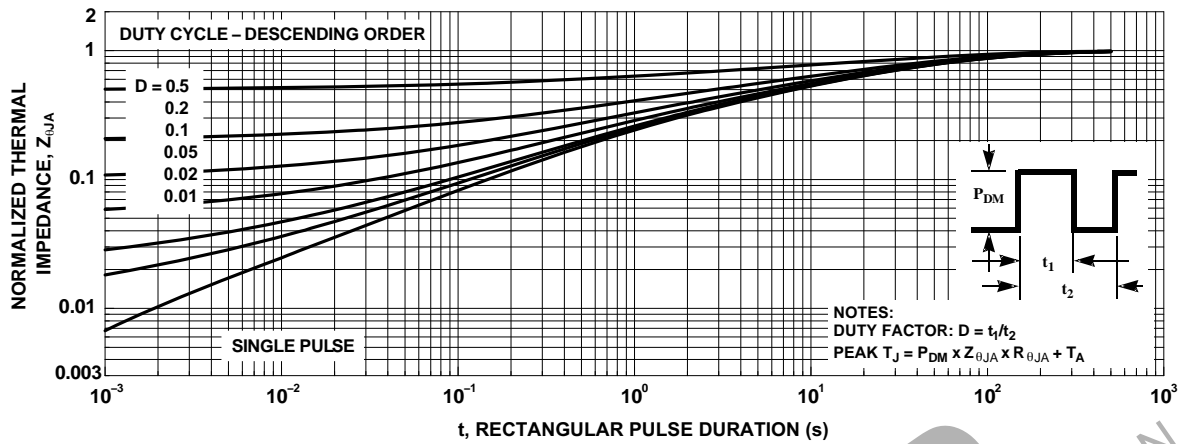


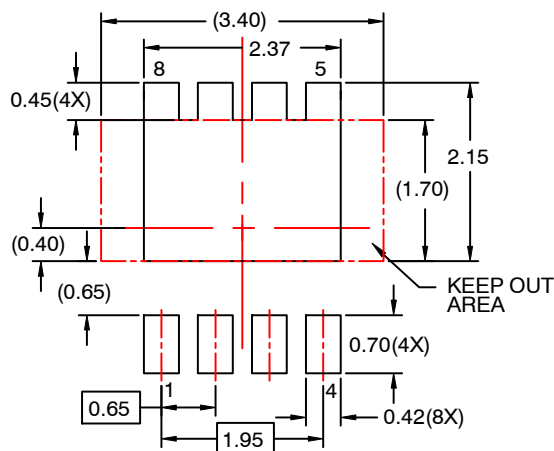
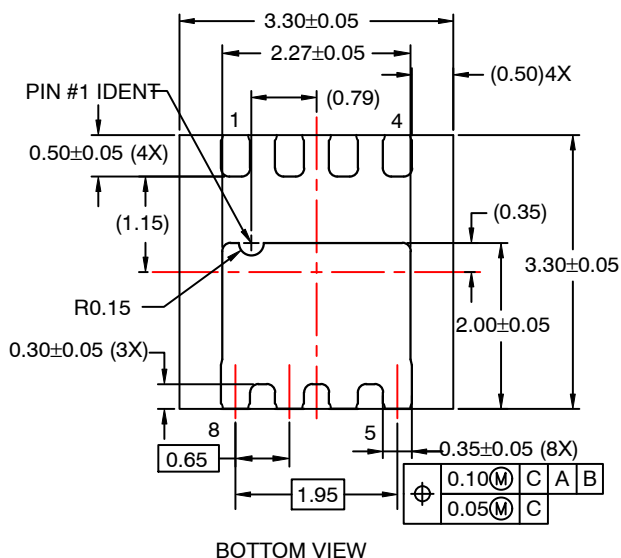
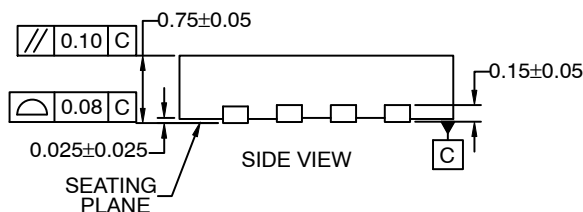
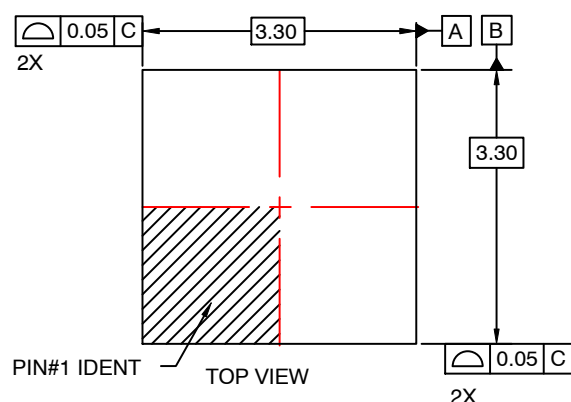
Figure 14. Gate Charge Characteristics

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

**DISCONTINUED**  
 THIS DEVICE IS NOT RECOMMENDED FOR NEW DESIGN  
 PLEASE CONTACT YOUR onsemi  
 REPRESENTATIVE FOR INFORMATION

WDFN8 3.3x3.3, 0.65P  
CASE 511DH  
ISSUE O

DATE 31 JUL 2016



## RECOMMENDED LAND PATTERN

NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.

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